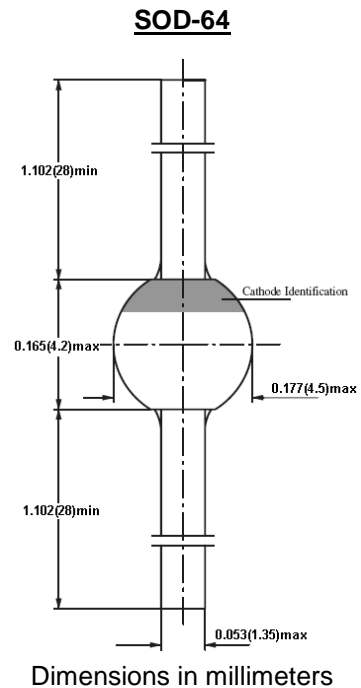


Features

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability

Mechanical Data

- Case: SOD-64 sintered glass case
- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Polarity: color band denotes cathode end
- Mounting position: any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

| | SYMBOL | BYM26C | units |
|---|----------------|-------------|-------------|
| Maximum Recurrent Peak Reverse Voltage | V_{RRM} | 600 | V |
| Maximum RMS Voltage | V_{RMS} | 420 | V |
| Maximum DC blocking Voltage | V_{DC} | 600 | V |
| Reverse Breakdown Voltage at $I_R = 0.1mA$ | $V_{(BR)R}$ | 700min | V |
| Maximum Average Forward Rectified Current and $T_{tp}=55^{\circ}C$; lead length=10mm | I_{FAV} | 2.3 | A |
| Peak Forward Surge Current at $t=10ms$ half sine wave | I_{FSM} | 45 | A |
| Maximum Forward Voltage at Rated Forward Current and 25°C $I_F = 2.0A$ | V_F | 2.65 | V |
| Maximum DC Reverse Current $T_a = 25^{\circ}C$ at rated DC blocking voltage $T_a = 150^{\circ}C$ | I_R | 10 150 | μA |
| Maximum Reverse Recovery Time (Note 1) | T_{rr} | 30 | nS |
| Non Repetitive Reverse Avalanche Energy | E_R | 10 | mJ |
| Diode Capacitance at $f=1MHz, V_R=0V$ | C_d | 85 | pF |
| Typical Thermal Resistance (Note 2) | $R_{th(ja)}$ | 75 | K/W |
| Storage and Operating Junction Temperature | T_{stg}, T_j | -65 to +175 | $^{\circ}C$ |

Note:

- Reverse Recovery Condition $I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A$
- Device mounted on an epoxy-glass printed-circuit board, 1.5mm thick; thickness of Cu-layer $\geq 40 \mu m$

RATINGS AND CHARACTERISTIC CURVES BYM26C

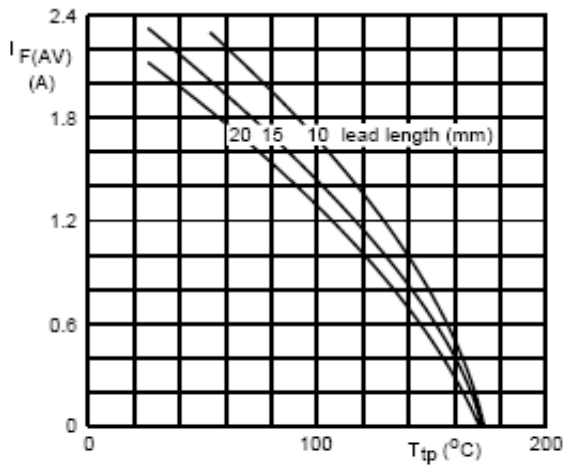


Fig. 1 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).

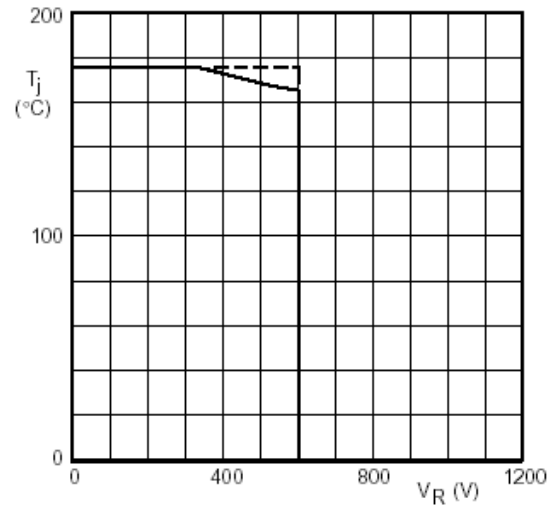


Fig. 2 Maximum permissible junction temperature as a function of reverse voltage.

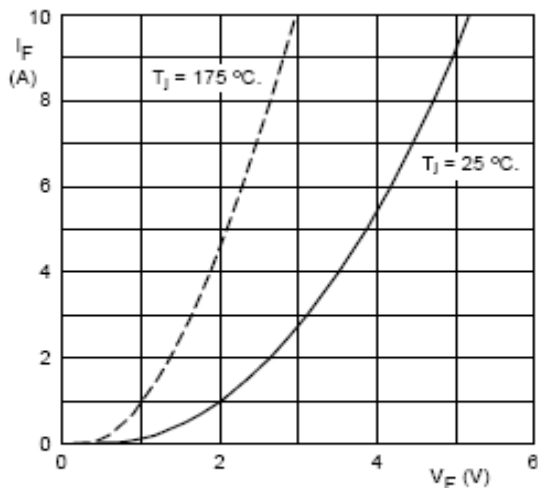


Fig. 3 Forward current as a function of forward voltage; maximum values.

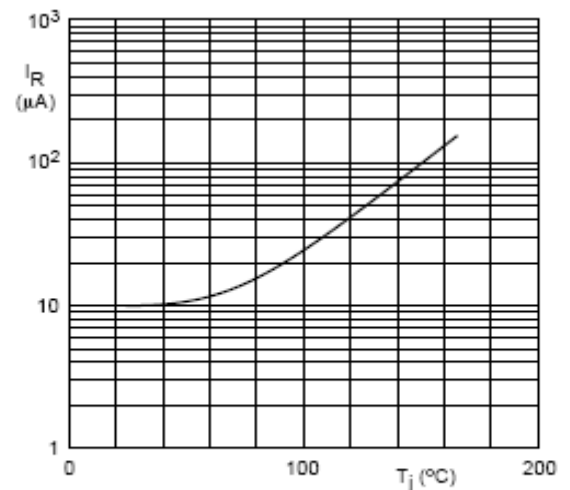


Fig. 4 Reverse current as a function of junction temperature; maximum values.

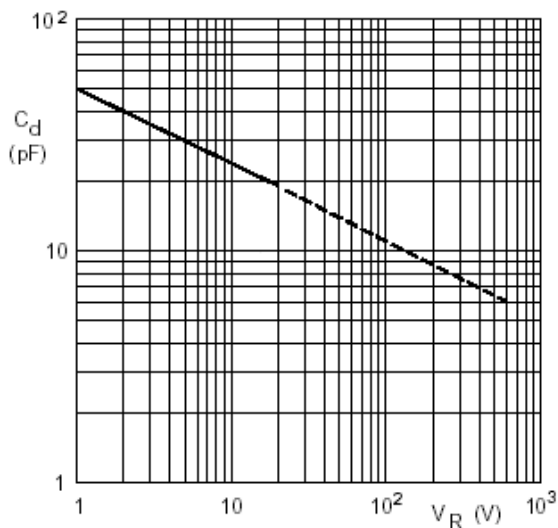


Fig.5 Diode capacitance as a function of reverse voltage; typical values.